

74LVC1G3157-Q100

2-channel analog multiplexer/demultiplexer

Rev. 1 — 19 February 2013

Product data sheet

1. General description

The 74LVC1G3157-Q100 provides one analog multiplexer/demultiplexer with one digital select input (S), two independent inputs/outputs (Y0, Y1) and a common input/output (Z).

Schmitt trigger action at the select input makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 1.65 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40°C to $+85^{\circ}\text{C}$ and from -40°C to $+125^{\circ}\text{C}$
- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
 - ◆ 7.5 Ω (typical) at $V_{CC} = 2.7\text{ V}$
 - ◆ 6.5 Ω (typical) at $V_{CC} = 3.3\text{ V}$
 - ◆ 6 Ω (typical) at $V_{CC} = 5\text{ V}$
- Switch current capability of 32 mA
- Break-before-make switching
- High noise immunity
- CMOS low power consumption
- TTL interface compatibility at 3.3 V
- Latch-up performance meets requirements of JESD 78 Class I
- Control input accepts voltages up to 5.5 V
- Multiple package options
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)



3. Ordering information

Table 1. Ordering information

Type number	Package	Temperature range	Name	Description	Version
74LVC1G3157GW-Q100	SC-88	–40 °C to +125 °C		plastic surface-mounted package; 6 leads	SOT363
74LVC1G3157GV-Q100	SC-74	–40 °C to +125 °C		plastic surface-mounted package (TSOP6); 6 leads	SOT457
74LVC1G3157GM-Q100	XSON6	–40 °C to +125 °C		plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886

4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74LVC1G3157GW-Q100	YJ
74LVC1G3157GV-Q100	YJ
74LVC1G3157GM-Q100	YJ

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

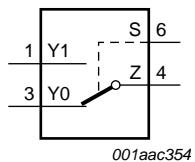


Fig 1. Logic symbol

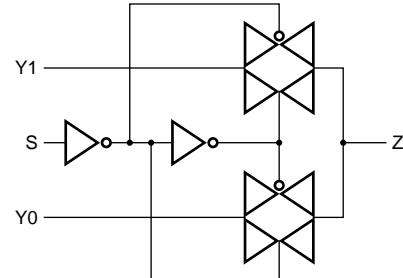


Fig 2. Logic diagram

6. Pinning information

6.1 Pinning

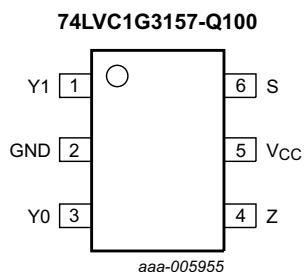


Fig 3. Pin configuration SOT363 and SOT457

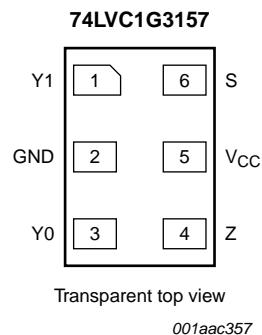


Fig 4. Pin configuration SOT886

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Y1	1	independent input or output
GND	2	ground (0 V)
Y0	3	independent input or output
Z	4	common output or input
Vcc	5	supply voltage
S	6	select input

7. Functional description

Table 4. Function table^[1]

Input S	Channel on
L	Y0
H	Y1

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
V _I	input voltage		[1] -0.5	+6.5	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-50	-	mA
I _{SK}	switch clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±50	mA
V _{SW}	switch voltage	enable and disable mode	[2] -0.5	V _{CC} + 0.5	V
I _{SW}	switch current	V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{STG}	storage temperature		-65	+150	°C
P _{TOT}	total power dissipation	T _{AMB} = -40 °C to +125 °C	[3] -	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For SC-88 and SC-74 packages: above 87.5 °C the value of P_{TOT} derates linearly with 4.0 mW/K.

For XSON6 package: above 118 °C the value of P_{TOT} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
V _I	input voltage		0	-	5.5	V
V _{SW}	switch voltage	enable and disable mode	[1] 0	-	V _{CC}	V
T _{AMB}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	[2] -	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	[2] -	-	10	ns/V

[1] To avoid sinking GND current from terminal Z when switch current flows in terminal Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current flows from terminal Yn. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

10. Static characteristics

Table 7. Static characteristics

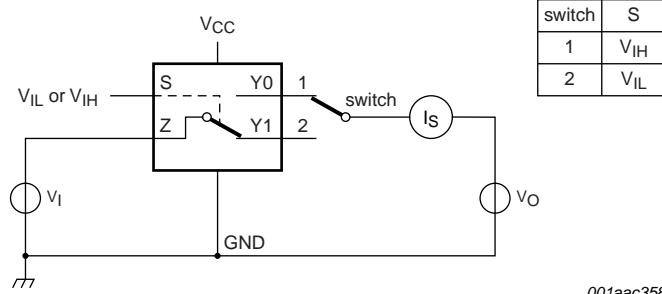
At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65V _{CC}	-	-	0.65V _{CC}	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 3 V to 3.6 V	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	0.7V _{CC}	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35V _{CC}	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 3 V to 3.6 V	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3V _{CC}	-	0.3V _{CC}	V
I _I	input leakage current	pin S; V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	[2]	-	±0.1	±2	-	±10 μA
I _{S(OFF)}	OFF-state leakage current	V _{CC} = 5.5 V; see Figure 5	[2]	-	±0.1	±5	-	±20 μA
I _{S(ON)}	ON-state leakage current	V _{CC} = 5.5 V; see Figure 6	[2]	-	±0.1	±5	-	±20 μA
I _{CC}	supply current	V _I = 5.5 V or GND; V _{SW} = GND or V _{CC} ; V _{CC} = 1.65 V to 5.5 V	[2]	-	0.1	10	-	40 μA
ΔI _{CC}	additional supply current	pin S; V _I = V _{CC} − 0.6 V; V _{CC} = 5.5 V; V _{SW} = GND or V _{CC}	[2]	-	5	500	-	5000 μA
C _I	input capacitance		-	2.5	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance		-	6.0	-	-	-	pF
C _{S(ON)}	ON-state capacitance		-	18	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

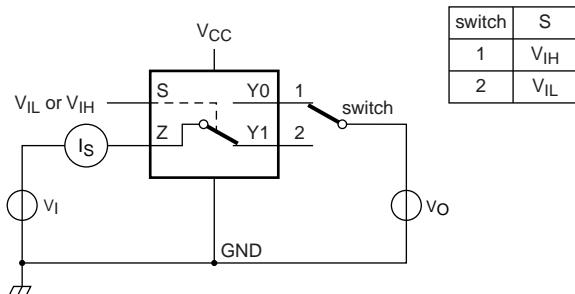
[2] These typical values are measured at V_{CC} = 3.3 V

10.1 Test circuits



$V_I = V_{CC}$ or GND and $V_O = GND$ or V_{CC} .

Fig 5. Test circuit for measuring OFF-state leakage current



$V_I = V_{CC}$ or GND and $V_O = \text{open circuit}$.

Fig 6. Test circuit for measuring ON-state leakage current

10.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 8](#) to [Figure 13](#).

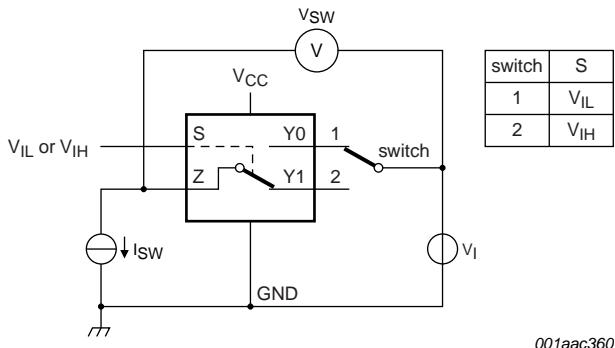
Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max		
R _{ON(peak)}	ON resistance (peak)	$V_I = GND$ to V_{CC} ; see Figure 7							
		$I_{SW} = 4\text{ mA}; V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	34.0	130	-	195	Ω	
		$I_{SW} = 8\text{ mA}; V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	12.0	30	-	45	Ω	
		$I_{SW} = 12\text{ mA}; V_{CC} = 2.7\text{ V}$	-	10.4	25	-	38	Ω	
		$I_{SW} = 24\text{ mA}; V_{CC} = 3\text{ V to }3.6\text{ V}$	-	7.8	20	-	30	Ω	
		$I_{SW} = 32\text{ mA}; V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	6.2	15	-	23	Ω	

Table 8. ON resistance ...continuedAt recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 8](#) to [Figure 13](#).

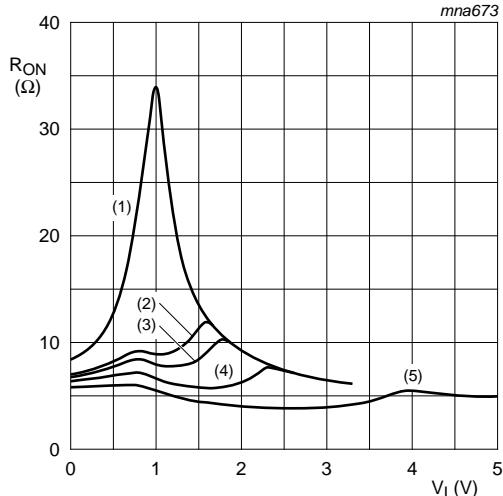
Symbol	Parameter	Conditions	-40 °C to +85 °C			Unit
			Min	Typ ^[1]	Max	
R _{ON(rail)}	ON resistance (rail)	V _I = GND; see Figure 7				
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	8.2	18	-
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	7.1	16	-
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	6.9	14	-
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	6.5	12	-
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	5.8	10	-
		V _I = V _{CC} ; see Figure 7				
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	10.4	30	-
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	7.6	20	-
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	7.0	18	-
R _{ON(flat)}	ON resistance (flatness)	V _I = GND to V _{CC}	[2]			
		I _{SW} = 4 mA; V _{CC} = 1.65 V to 1.95 V	-	26.0	-	-
		I _{SW} = 8 mA; V _{CC} = 2.3 V to 2.7 V	-	5.0	-	-
		I _{SW} = 12 mA; V _{CC} = 2.7 V	-	3.5	-	-
		I _{SW} = 24 mA; V _{CC} = 3 V to 3.6 V	-	2.0	-	-
		I _{SW} = 32 mA; V _{CC} = 4.5 V to 5.5 V	-	1.5	-	-

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

10.3 ON resistance test circuit and graphs



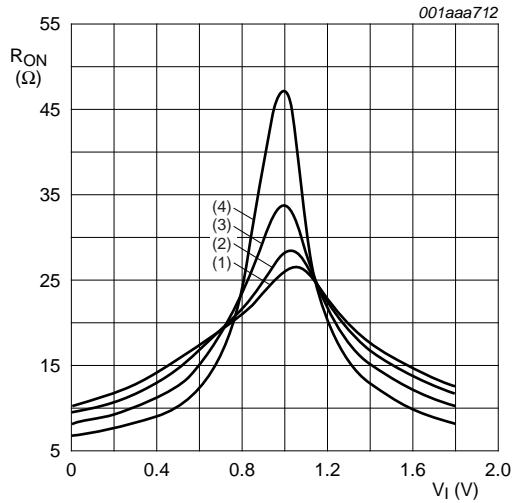
$$R_{ON} = V_{SW} / I_{SW}.$$



- (1) $V_{CC} = 1.8 \text{ V.}$
- (2) $V_{CC} = 2.5 \text{ V.}$
- (3) $V_{CC} = 2.7 \text{ V.}$
- (4) $V_{CC} = 3.3 \text{ V.}$
- (5) $V_{CC} = 5.0 \text{ V.}$

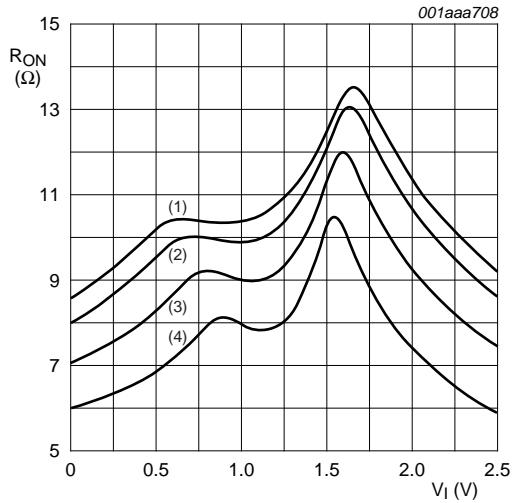
Fig 7. Test circuit for measuring ON resistance

Fig 8. Typical ON resistance as a function of input voltage; $T_{amb} = 25 \text{ }^{\circ}\text{C}$



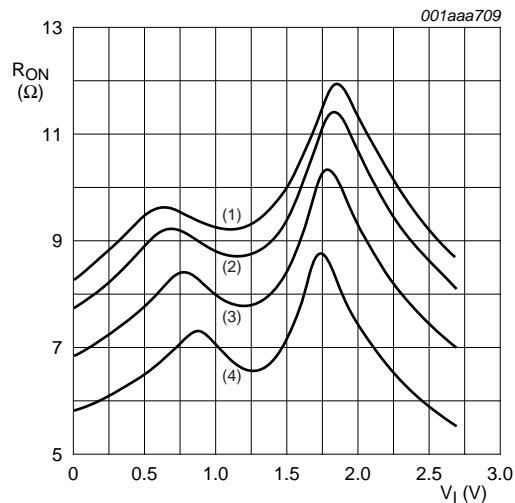
- (1) $T_{amb} = 125 \text{ }^{\circ}\text{C.}$
- (2) $T_{amb} = 85 \text{ }^{\circ}\text{C.}$
- (3) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$
- (4) $T_{amb} = -40 \text{ }^{\circ}\text{C.}$

Fig 9. ON resistance as a function of input voltage; $V_{CC} = 1.8 \text{ V}$



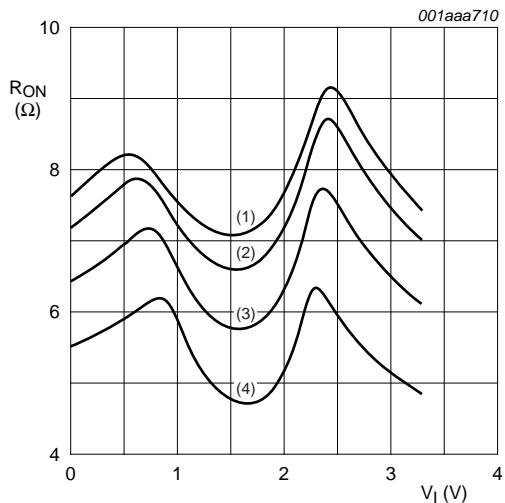
- (1) $T_{amb} = 125 \text{ }^{\circ}\text{C.}$
- (2) $T_{amb} = 85 \text{ }^{\circ}\text{C.}$
- (3) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$
- (4) $T_{amb} = -40 \text{ }^{\circ}\text{C.}$

Fig 10. ON resistance as a function of input voltage; $V_{CC} = 2.5 \text{ V}$



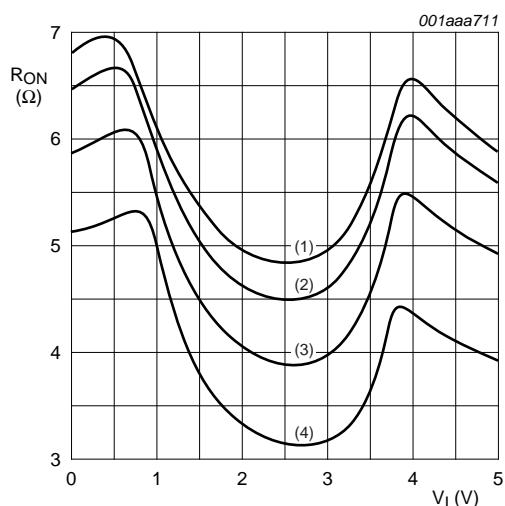
- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85$ °C.
- (3) $T_{amb} = 25$ °C.
- (4) $T_{amb} = -40$ °C.

Fig 11. ON resistance as a function of input voltage; $V_{CC} = 2.7$ V



- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85$ °C.
- (3) $T_{amb} = 25$ °C.
- (4) $T_{amb} = -40$ °C.

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 3.3$ V



- (1) $T_{amb} = 125$ °C.
- (2) $T_{amb} = 85$ °C.
- (3) $T_{amb} = 25$ °C.
- (4) $T_{amb} = -40$ °C.

Fig 13. ON resistance as a function of input voltage; $V_{CC} = 5.0$ V

11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 17](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay	Z to Yn or Yn to Z; see Figure 14 ^{[2][3]}						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	-	2	-	3.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	1.2	-	2.0	ns
		$V_{CC} = 2.7 \text{ V}$	-	-	1.0	-	1.5	ns
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	-	-	0.8	-	1.5	ns
t_{en}	enable time	S to Yn; see Figure 15 ^[4]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.0	8.7	14	1.0	14.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.0	5.3	7.5	1.0	7.5	ns
		$V_{CC} = 2.7 \text{ V}$	1.0	4.9	6.0	1.0	6.0	ns
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	0.5	4.0	5.5	0.5	5.5	ns
t_{dis}	disable time	S to Yn; see Figure 15 ^[5]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.5	6.0	8.5	2.5	8.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.0	4.4	6.0	2.0	6.0	ns
		$V_{CC} = 2.7 \text{ V}$	1.5	4.2	5.0	1.5	5.0	ns
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	1.5	3.6	4.5	1.5	4.5	ns
t_{b-m}	break-before-make time	see Figure 16 ^[6]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.5	-	-	0.5	-	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	-	-	0.5	-	ns
		$V_{CC} = 2.7 \text{ V}$	0.5	-	-	0.5	-	ns
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	0.5	-	-	0.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	-	-	0.5	-	ns

[1] Typical values are measured at $T_{amb} = 25 \text{ }^{\circ}\text{C}$ and nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

[4] t_{en} is the same as t_{PZH} and t_{PZL} .

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[6] Break-before-make specified by design.

11.1 Waveforms and test circuits

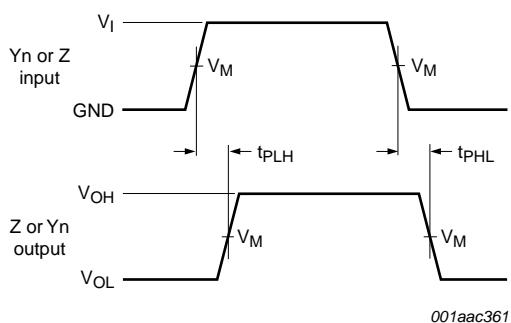


Fig 14. Input (Yn or Z) to output (Z or Yn) propagation delays

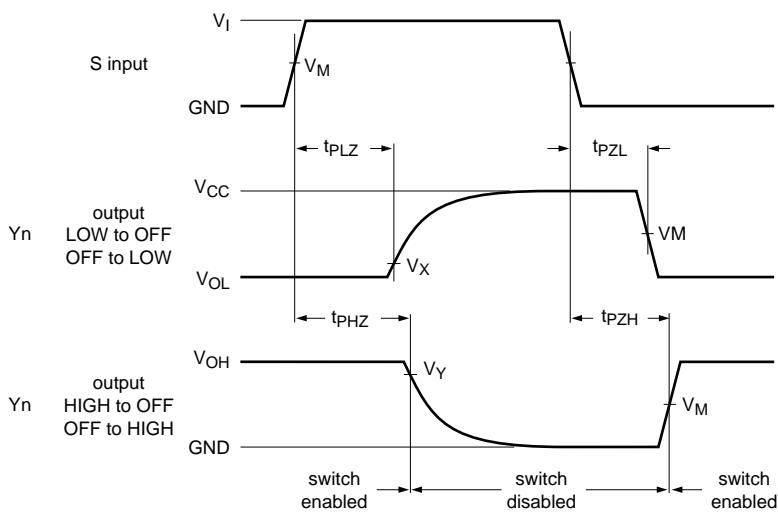
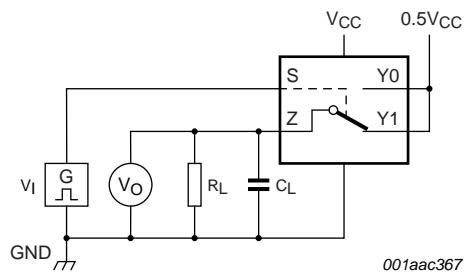


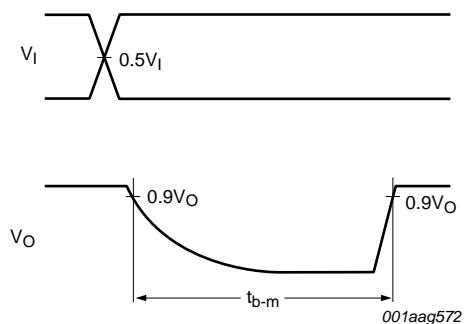
Fig 15. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC} 1.65 V to 5.5 V	V_M $0.5V_{CC}$	V_M $0.5V_{CC}$	V_X $V_{OL} + 0.3 \text{ V}$	V_Y $V_{OH} - 0.3 \text{ V}$

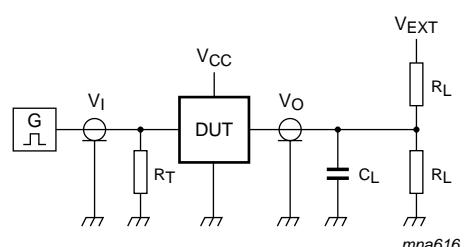


a. Test circuit



b. Input and output measurement points

Fig 16. Test circuit for measuring break-before-make timing



Test data is given in [Table 11](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

V_{EXT} = External voltage for measuring switching times.

Fig 17. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load		V _{EXT}		
V _{CC}	V _I	t _r , t _f	C _L	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	50 pF	500 Ω	open	GND	2V _{CC}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	50 pF	500 Ω	open	GND	2V _{CC}
2.7 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2V _{CC}
3 V to 3.6 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2V _{CC}
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2V _{CC}

11.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	f _i = 600 Hz to 20 kHz; R _L = 600 Ω; C _L = 50 pF; V _I = 0.5 V (p-p); see Figure 18	-	0.260	-	%
		V _{CC} = 1.65 V	-	0.078	-	%
		V _{CC} = 2.3 V	-	0.078	-	%
		V _{CC} = 3.0 V	-	0.078	-	%
		V _{CC} = 4.5 V	-	0.078	-	%
f _(-3dB)	-3 dB frequency response	R _L = 50 Ω; C _L = 5 pF; see Figure 19	-	200	-	MHz
		V _{CC} = 1.65 V	-	300	-	MHz
		V _{CC} = 2.3 V	-	300	-	MHz
		V _{CC} = 3.0 V	-	300	-	MHz
		V _{CC} = 4.5 V	-	300	-	MHz
α _{iso}	isolation (OFF-state)	R _L = 50 Ω; C _L = 5 pF; f _i = 10 MHz; see Figure 20	-	-42	-	dB
		V _{CC} = 1.65 V	-	-42	-	dB
		V _{CC} = 2.3 V	-	-40	-	dB
		V _{CC} = 3.0 V	-	-40	-	dB
		V _{CC} = 4.5 V	-	-40	-	dB
Q _{inj}	charge injection	C _L = 0.1 nF; V _{gen} = 0 V; R _{gen} = 0 Ω; f _i = 1 MHz; R _L = 1 MΩ; see Figure 21	-	3.3	-	pC
		V _{CC} = 1.8 V	-	4.1	-	pC
		V _{CC} = 2.5 V	-	5.0	-	pC
		V _{CC} = 3.3 V	-	6.4	-	pC
		V _{CC} = 4.5 V	-	7.5	-	pC
		V _{CC} = 5.5 V	-	-	-	-

11.3 Test circuits

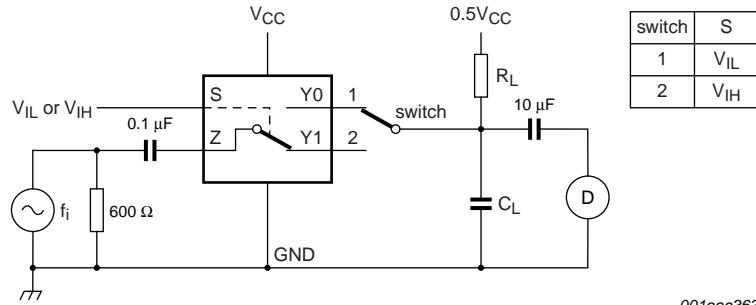
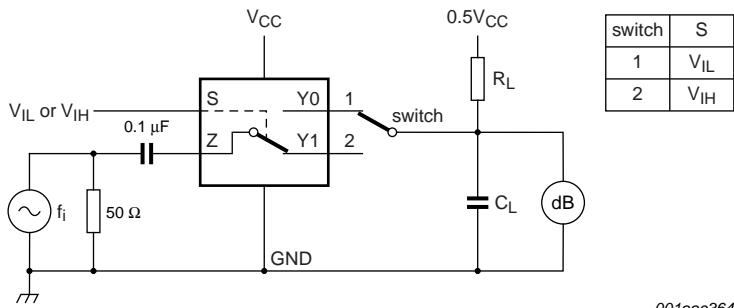
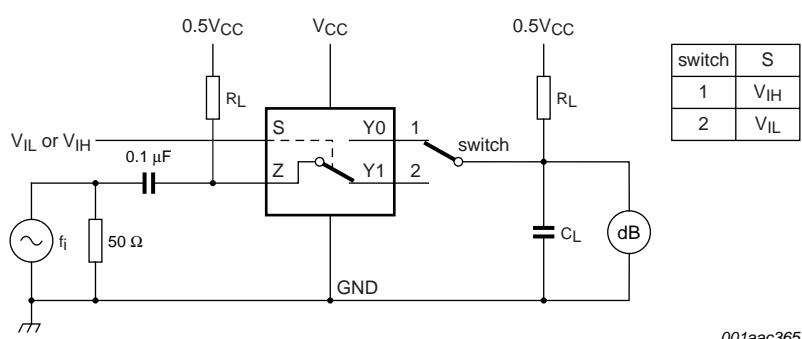


Fig 18. Test circuit for measuring total harmonic distortion



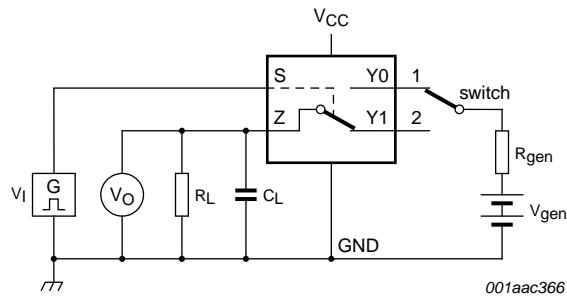
To obtain 0 dBm level at input, adjust f_i voltage. Increase f_i frequency until dB meter reads -3 dB.

Fig 19. Test circuit for measuring the frequency response when switch is in ON-state

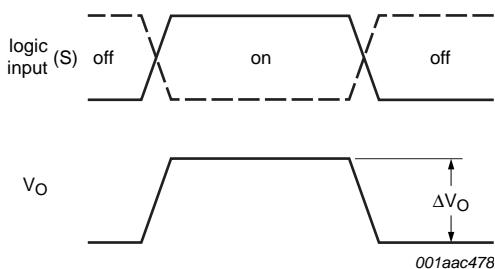


To obtain 0 dBm level at input, adjust f_i voltage

Fig 20. Test circuit for measuring isolation (OFF-state)



a. Test circuit



b. Input and output pulse definitions

$$Q_{\text{inj}} = \Delta V_O \times C_L$$

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

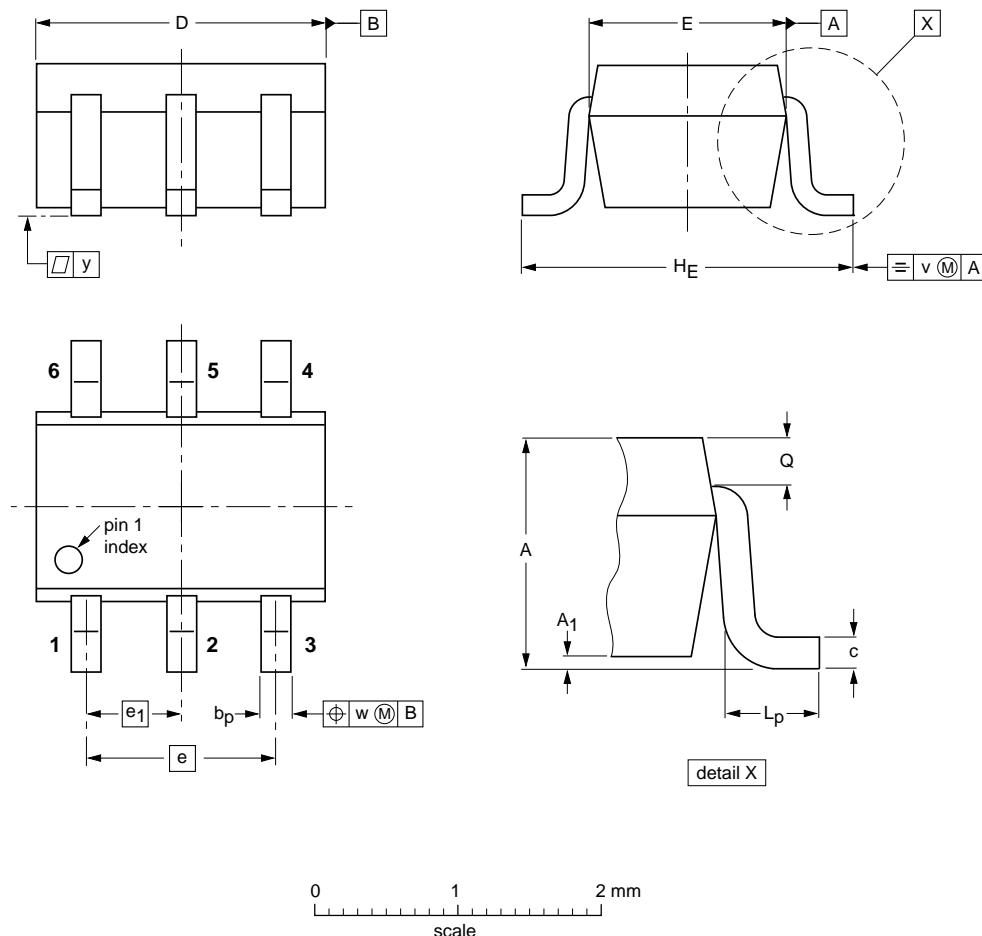
V_{gen} = generator voltage.

Fig 21. Test circuit for measuring charge injection

12. Package outline

Plastic surface-mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA	SC-88		
SOT363				SC-88		-04-11-08- 06-03-16

Fig 22. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

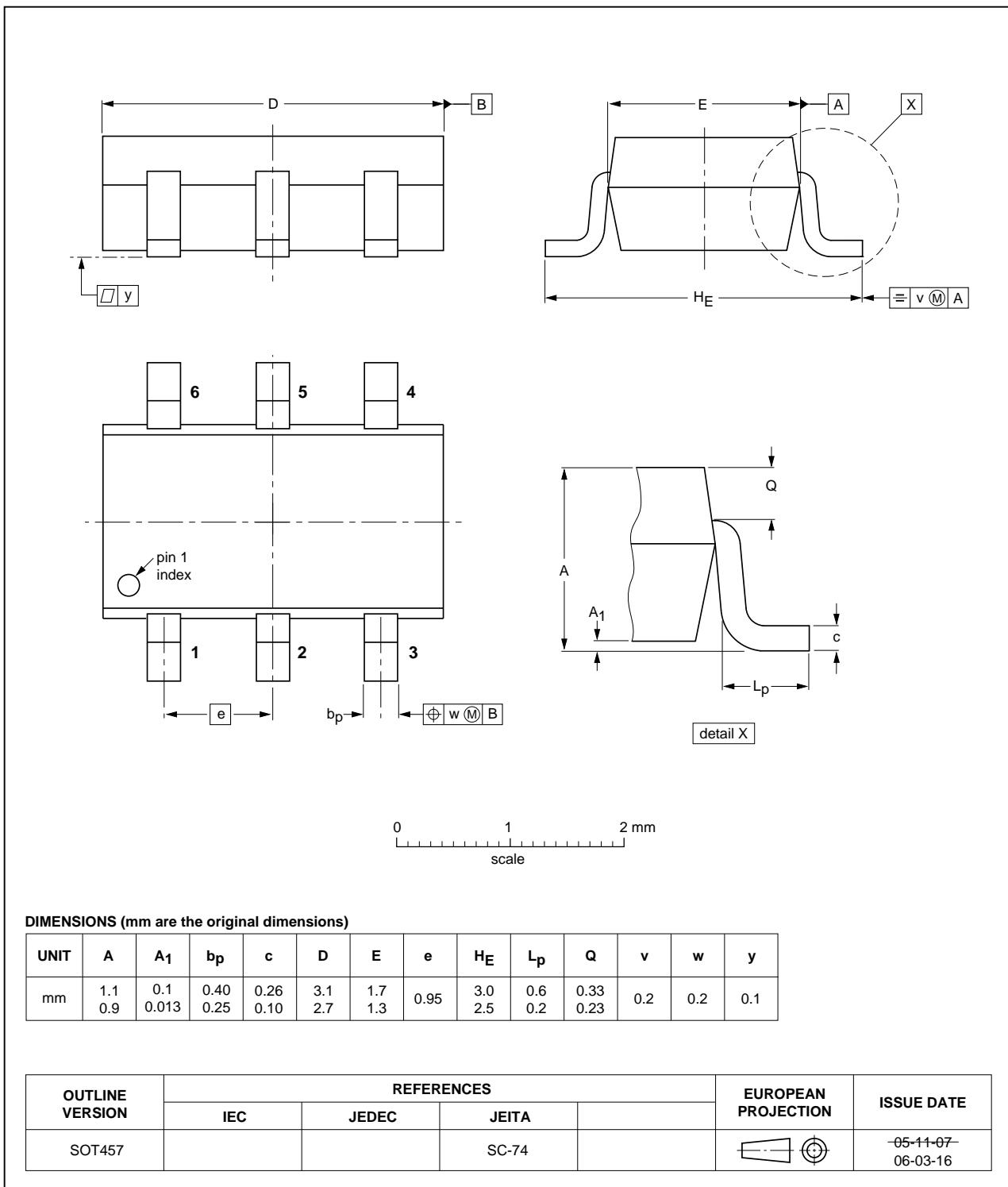


Fig 23. Package outline SOT457 (SC-74)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm

SOT886

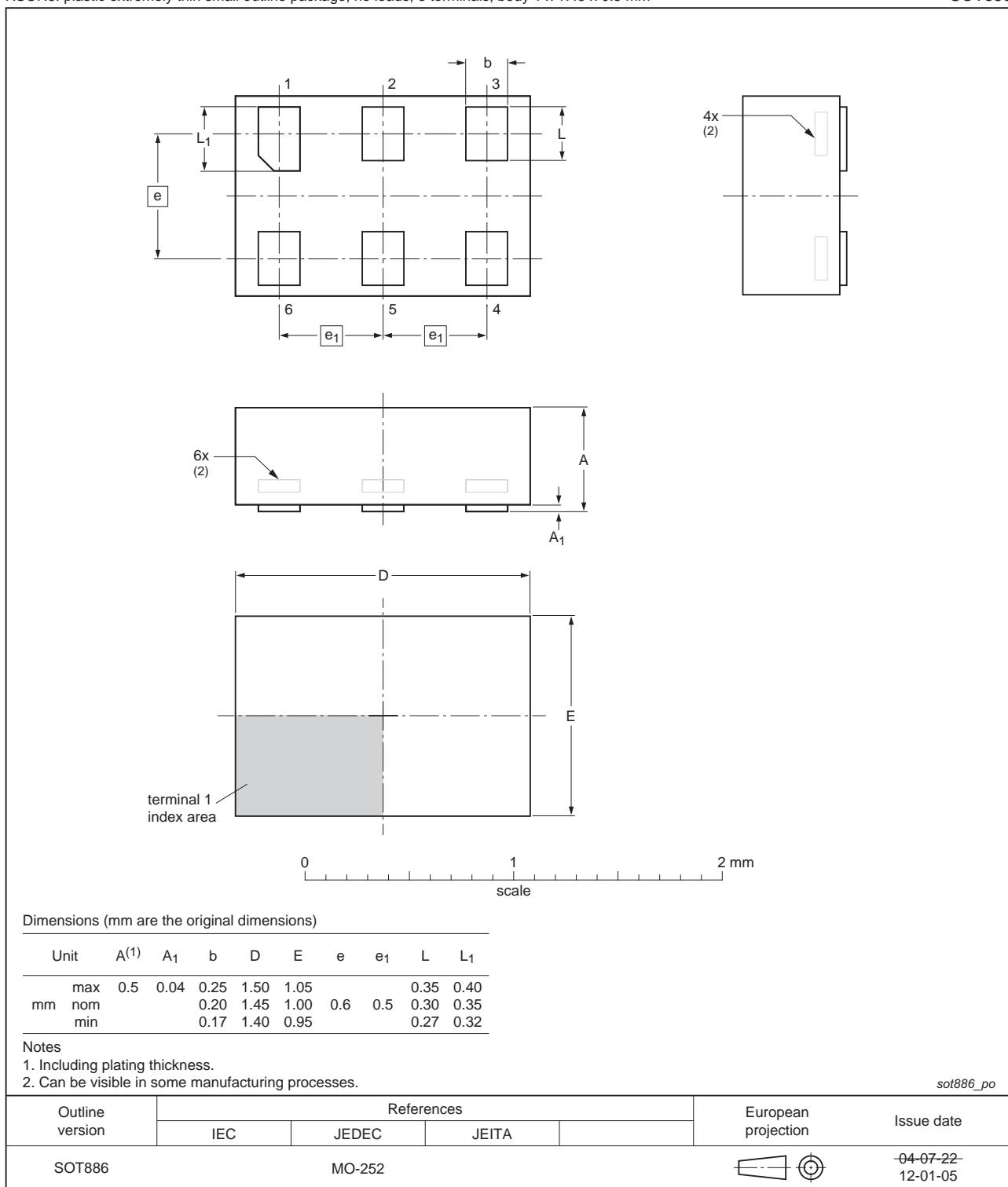


Fig 24. Package outline SOT886 (XSON6)

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military
DUT	Device Under Test

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G3157_Q100 v.1	20130219	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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